

## LISTING of CLAIMS

1-12. (Cancelled)

13. (Currently amended) A process for selectively removing silicon dioxide and photoresist sidewall residue after drywall etching of a semiconductor wafer comprising treating the wafer after dry etching with a solution comprising consisting essentially of;

- (a) sulfuric acid,
- (b) a fluorine containing compound hydrofluoric acid, ammonium fluoride or an alkali metal fluoride,

and

- (c) hydrogen peroxide,

wherein said solution contacts said sidewall residue effectively to remove it from said dry etched wafer,

and wherein the ratio (a):(b) is in the range of from 10:1 to 700:1 by weight.

14. (Currently amended) A process for removing photoresist according to claim 13, wherein the photoresist is effective for g-line, i-line, deep UV, E-beam or X-ray.

15. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated at a temperature of from 0 to 140 degrees C.

16. (Currently amended) A process for removing photoresist after dry etching according to claim 13, wherein the wafer is treated for about 10 minutes.

17. (Currently amended) A process for removing photoresist after dry etching according to claim 13, wherein the operation pressure is maintained at about 1 atm.

18. (Previously presented) A process for removing photoresist after dry etching according to claim 13, wherein the etch rate of the wafer is less than 1 Å/min.
19. (Currently amended) A process for removing photoresist after dry etching according to claim 15, wherein the wafer is treated at a temperature of from 120 to 140 degrees C.
20. (Previously presented) A process for removing photoresist after drywall etching according to claim 13, wherein the fluorine containing compound is hydrofluoric acid.
21. (Previously presented) A process for removing photoresist after drywall etching according to claim 20, wherein the ratio of sulfuric acid to hydrofluoric acid and hydrogen peroxide is 3:1 by volume.
22. (Cancel)
23. (Cancel)